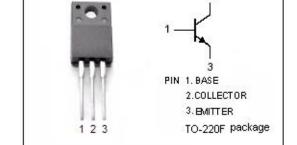


# **isc Silicon NPN Power Transistor**

2SD1408

### **DESCRIPTION**

- · Low Collector Saturation Voltage
- : V<sub>CE(sat)</sub>= 1.5V(Max)@ I<sub>C</sub>= 3A
- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 80V (Min)
- Complement to Type 2SB1017
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

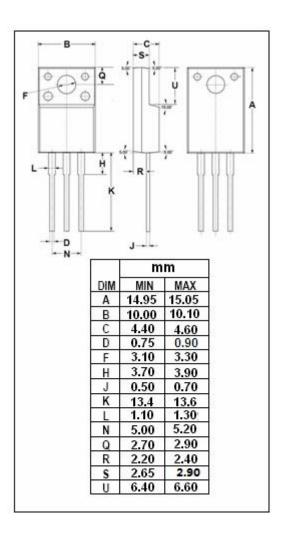


## **APPLICATIONS**

· Designed for power amplifier applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT		
V <sub>СВО</sub>	Collector-Base Voltage	ector-Base Voltage 80			
Vceo	Collector-Emitter Voltage	80	V		
V <sub>EBO</sub>	Emitter-Base Voltage	5	V		
Ic	Collector Current-Continuous 4		А		
lв	Base Current-Continuous	0.4	Α		
P <sub>C</sub>	Collector Power Dissipation @ Tc=25℃	25	W		
TJ	Junction Temperature	150	°C		
T <sub>stg</sub>	torage Temperature Range -55~150		$^{\circ}$		





## **isc Silicon NPN Power Transistor**

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### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =30mA ; I <sub>B</sub> = 0	80			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.3A			1.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 80V; I <sub>E</sub> = 0			30	μА
І <sub>ЕВО</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			0.1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V	40		240	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V	15	50		
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V, f <sub>test</sub> = 1MHz		90		pF
f <sub>⊤</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V		8		MHz

## ♦ h<sub>FE</sub> classifications

R	0	Y
40-80	70-140	120-240

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